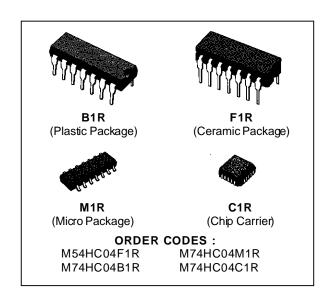
M54HC04 M74HC04

HEX INVERTER

- HIGH SPEED
 - $t_{PD} = 6 \text{ ns (TYP.)} AT V_{CC} = 5 \text{ V}$
- LOW POWER DISSIPATION $I_{CC} = 1 \mu A \text{ (MAX.)} \text{ AT } I_A = 25 \text{ °C}$
- HIGH NOISE IMMUNITY V_{NIH} = V_{NIL} = 28 % V_{CC} (MIN.)
- OUTPUT DRIVE CAPABILITY 10 LSTTL LOADS
- SYMMETRICAL OUTPUT IMPEDANCE | IOH | = I_{OL} = 4 mA (MIN.)
- BALANCED PROPAGATION DELAYS tplh = tphl
- WIDE OPERATING VOLTAGE RANGE Vcc (OPR) = 2 V TO 6 V
- PIN AND FUNCTION COMPATIBLE WITH 54/74LS04

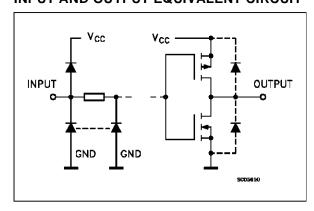


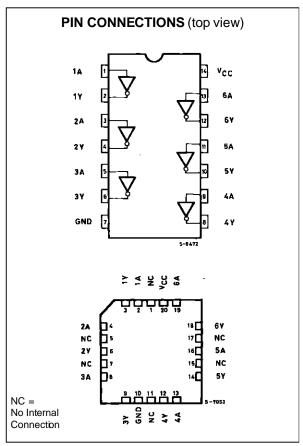
DESCRIPTION

The M54/74HC04 is a high speed CMOS HEX IN-VERTER fabricated in silicon gate C²MOS technology. It has the same high speed performance of LSTTL combined with true CMOS low power consumption.

The internal circuit is composed of 3 stages including buffer output, which enables high noise immunity and stable output. All inputs are equipped with circuits against static discharge and transient excess voltage.

INPUT AND OUTPUT EQUIVALENT CIRCUIT





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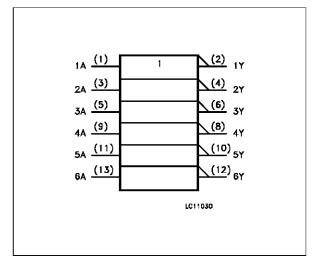
TRUTH TABLE

Α	Υ
L	Н
Н	L

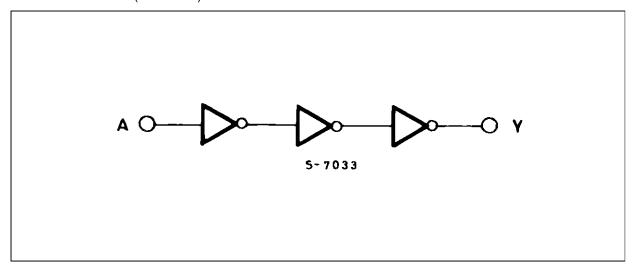
PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
1, 3, 5, 9, 11, 13	1A to 6A	Data Inputs
2, 4, 6, 8, 10, 12	1Y to 6Y	Data Outputs
7	GND	Ground (0V)
14	Vcc	Positive Supply Voltage

IEC LOGIC SYMBOL



LOGIC DIAGRAM (Per Gate)



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
Vcc	Supply Voltage	-0.5 to +7	V
Vı	DC Input Voltage	-0.5 to V _{CC} + 0.5	V
Vo	DC Output Voltage	-0.5 to V _{CC} + 0.5	V
lıĸ	DC Input Diode Current	± 20	mA
lok	DC Output Diode Current	± 20	mA
lo	DC Output Source Sink Current Per Output Pin	± 25	mA
I _{CC} or I _{GND}	DC V _{CC} or Ground Current	± 50	mA
P_{D}	Power Dissipation	500 (*)	mW
T _{stg}	Storage Temperature	-65 to +150	°C
T_L	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these condition is not implied. (*) 500 mW: \equiv 65 °C derate to 300 mW by 10mW/°C: 65 °C to 85 °C



RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit	
V_{CC}	Supply Voltage		2 to 6	V
V_{I}	Input Voltage	0 to V _{CC}	V	
Vo	Output Voltage	0 to V _{CC}	V	
T_{op}	Operating Temperature: M54HC Series M74HC Series		-55 to +125 -40 to +85	°C
t _r , t _f	Input Rise and Fall Time	V _{CC} = 2 V	0 to 1000	ns
		$V_{CC} = 4.5 \text{ V}$	0 to 500	
		$V_{CC} = 6 V$	0 to 400	

DC SPECIFICATIONS

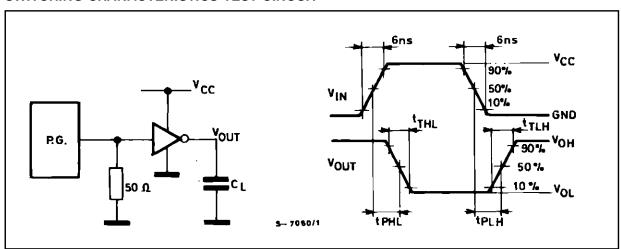
		Test Conditions					Value						
Symbol	Parameter	V _{CC} (V)			T _A = 25 °C 54HC and 74HC			85 °C HC	-55 to 125 °C 54HC		Unit		
		()			Min.	Тур.	Max.	Min.	Max.	Min.	Max.		
V_{IH}	High Level Input	2.0			1.5			1.5		1.5			
	Voltage	4.5			3.15			3.15		3.15		V	
		6.0			4.2			4.2		4.2			
V_{IL}	Low Level Input	2.0					0.5		0.5		0.5		
	Voltage	4.5					1.35		1.35		1.35	V	
		6.0					1.8		1.8		1.8		
VoH	High Level	2.0	V _I =	I _O =-20 μA	1.9	2.0		1.9		1.9		.,	
	Output Voltage	4.5			4.4	4.5		4.4		4.4			
		6.0	or		5.9	6.0		5.9		5.9		V	
		4.5	VIL	VIL	I _O =-4.0 mA	4.18	4.31		4.13		4.10		
		6.0		I _O =-5.2 mA	5.68	5.8		5.63		5.60			
V_{OL}	Low Level Output	2.0	Vı =			0.0	0.1		0.1		0.1		
	Voltage	4.5	VI =	I _O = 20 μA		0.0	0.1		0.1		0.1		
		6.0	or			0.0	0.1		0.1		0.1	V	
		4.5	V _{IL}	I _O = 4.0 mA		0.17	0.26		0.33		0.40		
		6.0		I _O = 5.2 mA		0.18	0.26		0.33		0.40		
I	Input Leakage Current	6.0	V _I = V _{CC} or GND				±0.1		±1		±1	μΑ	
Icc	Quiescent Supply Current	6.0	V _I = '	Vcc or GND			1		10		20	μΑ	

AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input $t_r = t_f = 6 \text{ ns}$)

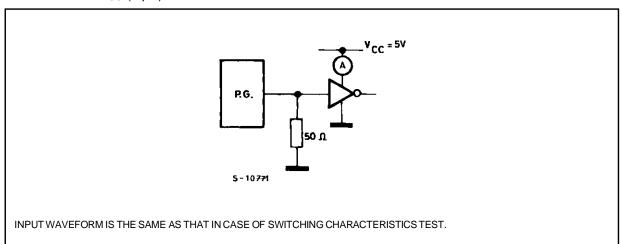
		Test Condit	tions	Value						
Symbol Parameter	Vcc		T _A = 25 °C 54HC and 74HC			-40 to 85 °C 74HC		-55 to 125 °C 54HC		
		(V)	Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
t_{TLH}	Output Transition	2.0		30	75		95		110	
t_{THL}	Time	4.5		8	15		19		22	ns
		6.0		7	13		16		19	
t _{PLH}	Propagation	2.0		27	75		95		110	
t_{PHL}	Delay Time	4.5		9	15		19		22	ns
		6.0		8	13		16		19	
C _{IN}	Input Capacitance			5	10		10		10	pF
C _{PD} (*)	Power Dissipation Capacitance			22						pF

^(*) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operting current can be obtained by the following equation. I_{CC}(opr) = C_{PD} • V_{CC} • f_{IN} + I_{CC}/6 (per Gate)

SWITCHING CHARACTERISTICS TEST CIRCUIT

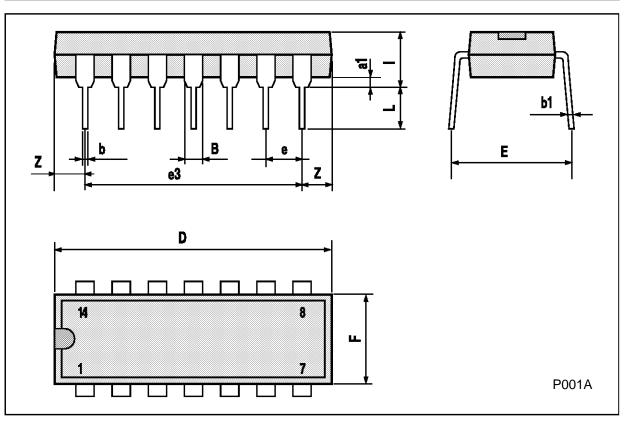


TEST CIRCUIT Icc (Opr.)



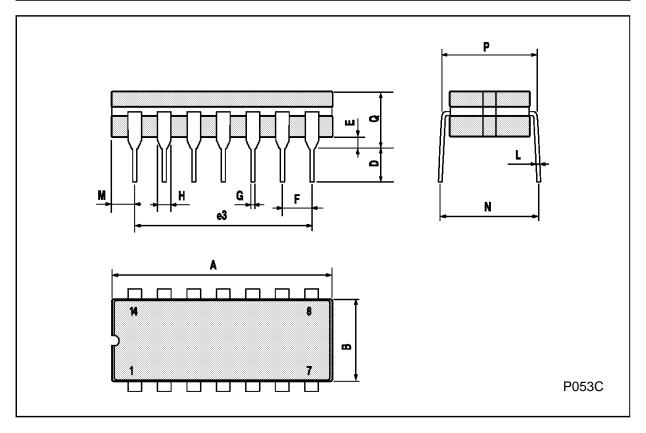
Plastic DIP14 MECHANICAL DATA

DIM.		mm		inch			
Dilli.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
a1	0.51			0.020			
В	1.39		1.65	0.055		0.065	
b		0.5			0.020		
b1		0.25			0.010		
D			20			0.787	
E		8.5			0.335		
е		2.54			0.100		
e3		15.24			0.600		
F			7.1			0.280	
I			5.1			0.201	
L		3.3			0.130		
Z	1.27		2.54	0.050		0.100	



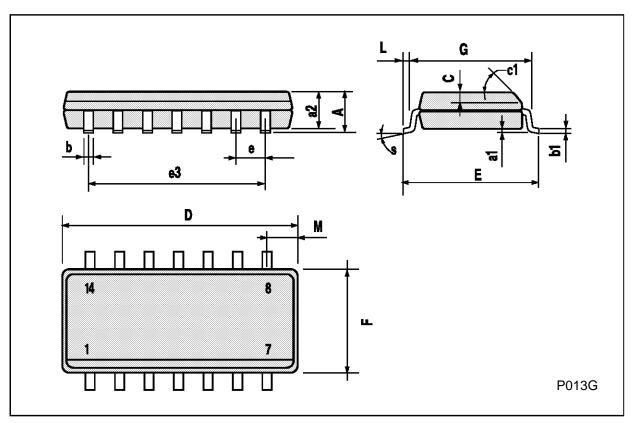
Ceramic DIP14/1 MECHANICAL DATA

DIM.		mm		inch			
Diwi.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
А			20			0.787	
В			7.0			0.276	
D		3.3			0.130		
Е	0.38			0.015			
e3		15.24			0.600		
F	2.29		2.79	0.090		0.110	
G	0.4		0.55	0.016		0.022	
H	1.17		1.52	0.046		0.060	
L	0.22		0.31	0.009		0.012	
М	1.52		2.54	0.060		0.100	
N			10.3			0.406	
Р	7.8		8.05	0.307		0.317	
Q			5.08			0.200	



SO14 MECHANICAL DATA

DIM.		mm		inch			
DIIVI.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
А			1.75			0.068	
a1	0.1		0.2	0.003		0.007	
a2			1.65			0.064	
b	0.35		0.46	0.013		0.018	
b1	0.19		0.25	0.007		0.010	
С		0.5			0.019		
c1			45° ((typ.)			
D	8.55		8.75	0.336		0.344	
E	5.8		6.2	0.228		0.244	
е		1.27			0.050		
e3		7.62			0.300		
F	3.8		4.0	0.149		0.157	
G	4.6		5.3	0.181		0.208	
L	0.5		1.27	0.019		0.050	
М			0.68			0.026	
S			8° (n	nax.)			



PLCC20 MECHANICAL DATA

DIM.		mm		inch			
Dilvi.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
А	9.78		10.03	0.385		0.395	
В	8.89		9.04	0.350		0.356	
D	4.2		4.57	0.165		0.180	
d1		2.54			0.100		
d2		0.56			0.022		
E	7.37		8.38	0.290		0.330	
е		1.27			0.050		
e3		5.08			0.200		
F		0.38			0.015		
G			0.101			0.004	
М		1.27			0.050		
M1		1.14			0.045		



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